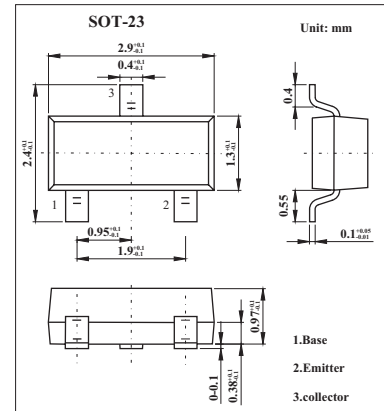


Switching Transistors

FMMT4126

■ Features

- Switching transistors.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-4	V
Collector current	I_C	-200	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FMMT4126

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=-10mA,	-25			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=-1mA,	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-10mA,	-4			V
Collector cutoff current	ICBO	VCE=-20V			-50	nA
Emitter cut-off current	IEBO	VEB=-3V			-50	nA
Collector-emitter saturation voltage *	VCE(sat)	Ic=-50mA, IB=-5mA			-0.4	V
Base-emitter saturation voltage *	VBE(sat)	Ic=-50mA, IB=-5mA			-0.95	V
DC current gain *	hFE	Ic=-2mA, VCE=-1V	120		360	
Current-gain-bandwidth product	fT	Ic=-10mA, VCE=-20V f=100MHz	250			MHz
Output capacitance	Cobo	VCB=-5V, IE=0, f=140KHz			4.5	pF
Input capacitance	Cibo	VBE=-0.5V, Ic=0, f=140KHz			10	pF
Noise figure	NF	VCE=-5V Ic=-200mA, Rg=-2K? f=30Hz to 15KHz at -3dB points			4	dB
Small signal current transfer	hfe	Ic=-2mA, VCE=-1V, f=1KHz	120	180		
Delay time	td	VCC=-3V, Ic=-10mA, IB1=-1mA			25	ns
Rise time	tr	VBE(off)=-0.5V			18	ns
Storage time	ts	VCC=-3V, Ic=-10mA			140	ns
Fall time	tf	IB1= IB2=-1mA			15	ns

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	ZE
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